L Number	Hits	Search Text	DB	Time stamp
1	2	("4967256").PN.	USPAT;	2002/06/11 11:03
'	_	(	US-PGPUB;	
	i	,	EPO; JPO;	
		,	IBM_TDB	
7	170	semiconductor and (surge adj protector)	USPAT;	2002/06/11 11:42
'	1,0	Serificonductor and (odigo daj protoctor)	US-PGPUB;	
]			EPO; JPO;	
1			IBM_TDB	
	200	emitter and base and buried and (surge overvoltage)	USPAT;	2002/06/11 13:20
13	300	emiller and base and buried and (surge overvoltage)	US-PGPUB;	
, ,			EPO; JPO;	
1			IBM_TDB	
l		( ''' ) the second busined and (ourse over oltogo) and	USPAT;	2002/06/11 12:22
19	3	(emitter and base and buried and (surge overvoltage)) and		2002/00/11 12.22
		(semiconductor and (surge adj protector))	US-PGPUB;	
1			EPO; JPO;	
			IBM_TDB	0000/06/44 40:30
25	2	("5001537").PN.	USPAT;	2002/06/11 12:32
			US-PGPUB;	
			EPO; JPO;	
		•	IBM_TDB	
31	1	("5479031").PN.	USPAT;	2002/06/11 12:32
		,	US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
37	12	emitter and base and buried and (surge overvoltage) and	USPAT;	2002/06/11 14:03
		moat and ( oxide dielectric)	US-PGPUB;	
		,	EPO; JPO;	
			IBM_TDB	
43	12	(moat emitter) and base and buried and (surge overvoltage)	USPAT;	2002/06/11 14:07
70	,-	and moat and ( oxide dielectric)	US-PGPUB;	
		and mode and ( oxide diolocate)	EPO; JPO;	
]			IBM TDB	
49	0	((moat adj emitter) ( tench adj emitter)) and base and buried	USPAT;	2002/06/11 14:43
49	١	and (surge overvoltage) and moat and ( oxide dielectric)	US-PGPUB;	
		and (surge overvoitage) and mout and ( exact are exact)	EPO; JPO;	
l	İ		IBM_TDB	
	1	((moat adj emitter) ( tench adj emitter)) and base and buried	USPAT;	2002/06/11 14:59
55			US-PGPUB;	
		and moat and ( oxide dielectric)	EPO; JPO;	
			IBM_TDB	
	400	(/t	USPAT;	2002/06/11 15:31
61	168	((moat adj&? emitter) ( tench adj emitter)) and base and		2002/00/17 10:01
		buried and moat and ( oxide dielectric)	EPO; JPO;	[
1			IBM TDB	
		,, , , , , , , , , , , , , , , , , , ,	USPAT:	2002/06/11 15:46
67	1	((moat adj emitter) ( tench adj emitter)) and base and buried	US-PGPUB;	2302/00/11 10.40
		and moat and ( oxide dielectric)		
			EPO; JPO;	
1			IBM_TDB	2002/06/11 15:51
73	2	((moat adj emitter) ( tench adj emitter))	USPAT;	2002/00/11 15.51
	1		US-PGPUB;	1
			EPO; JPO;	
			IBM_TDB	0000/00/44 40 40
79	2	emitter near moat	USPAT;	2002/06/11 16:12
			US-PGPUB;	
			EPO; JPO;	
	1		IBM_TDB	
85	89	emitter and moat and (diffusion implant) and oxide and filled	USPAT;	2002/06/11 16:15
1			US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
L	<u></u>			1